

TO-251-3L Plastic-Encapsulate Transistors

MJD41C TRANSISTOR (NPN)

FEATURES

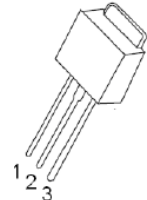
- Designed for General Purpose Amplifier and Low Speed Switching Applications.
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Lead Formed Version in 16 mm Tape and Reel (“T4” Suffix)
- Electrically Similar to Popular TIP41 and TIP42 Series
- Monolithic Construction With Built-in Base-Emitter Resistors

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	6	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-65-150	°C

TO-251-3L

- 1.BASE
2.COLLECTOR
3.EMITTER



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	100			V
Collector-emitter breakdown voltage	V _{CEO(sus)}	I _C =30mA, I _B =0	100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CEO}	V _{CB} =60V, I _E =0			50	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.5	mA
DC current gain	h _{FE(1)}	V _{CE} =4V, I _C =0.3A	30			
	h _{FE(2)}	V _{CE} =4V, I _C =3A	15		75	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =6A, I _B =0.6A			1.5	V
Base-emitter voltage	V _{BE}	V _{CE} =4V, I _C =6A			2	V
Transition frequency	f _T	V _{CE} =10V, I _C =500mA, f=1MHz	3			MHz

